



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

NISHIMOTO et al

Serial No.: 08/897,839

Filed: July 21, 1997

For: STRESS-ADJUSTED INSULATING  
FILM FORMING METHOD,  
SEMICONDUCTOR DEVICE AND  
METHOD OF MANUFACTURING THE  
SAME

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) Art Unit: 2823  
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) Examiner: K. Eaton  
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RESPONSE TO FINAL ACTION UNDER 37 CFR 1.116

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

Responsive to the final action of July 12, 2002, please amend the captioned application as follows:

IN THE CLAIMS:

Please cancel claims 44-46 and rewrite claims 43 and 47 as follows:

43. (Twice Amended) A stress-adjusted insulating film forming method for forming a multilayered insulating film on a substrate, said method comprising:

(a) forming a first insulating layer with compressive stress;

TC 2800 MAIL ROOM

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J. McMillan

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